

The Impact of Electro- Thermal Coupling on RF Power Amplifiers

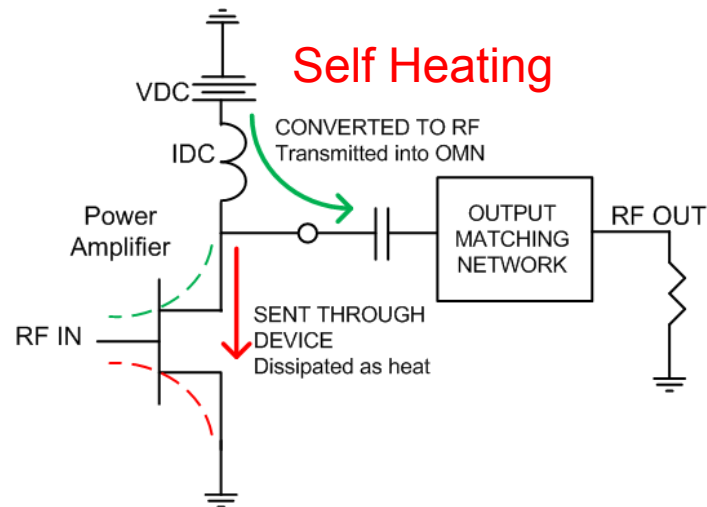
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Review of Heating in Active Devices:

Self Heating
Mutual Heating
Transient Heating

(+ different approaches to modeling these)

Device Heating Basics:

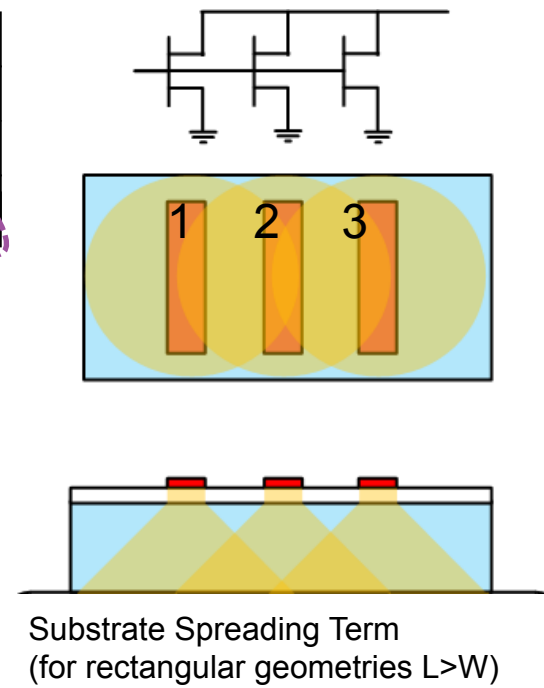


Self Heating Terms

$$R_{ij} = \begin{bmatrix} R_{11} & R_{12} & R_{13} \\ R_{21} & R_{22} & R_{23} \\ R_{31} & R_{32} & R_{33} \end{bmatrix}$$

$$R_{ij} = \frac{\Delta T_i}{\Delta P_j}$$

Mutual Heating



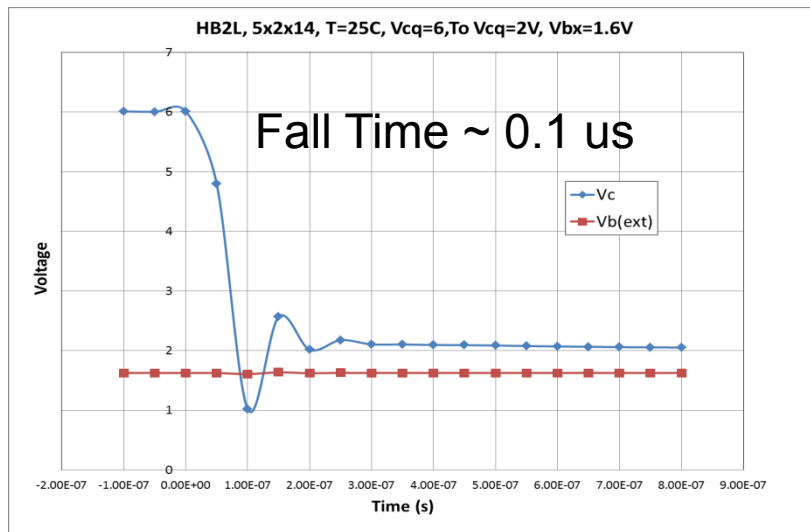
$$T_{device} = T_{ambient} + R_{th} * P_{diss}$$

$$R_{th} = \frac{1}{2\kappa(L-W)} \ln \left(\frac{L(W + 2t_{sub})}{W(L + 2t_{sub})} \right)$$

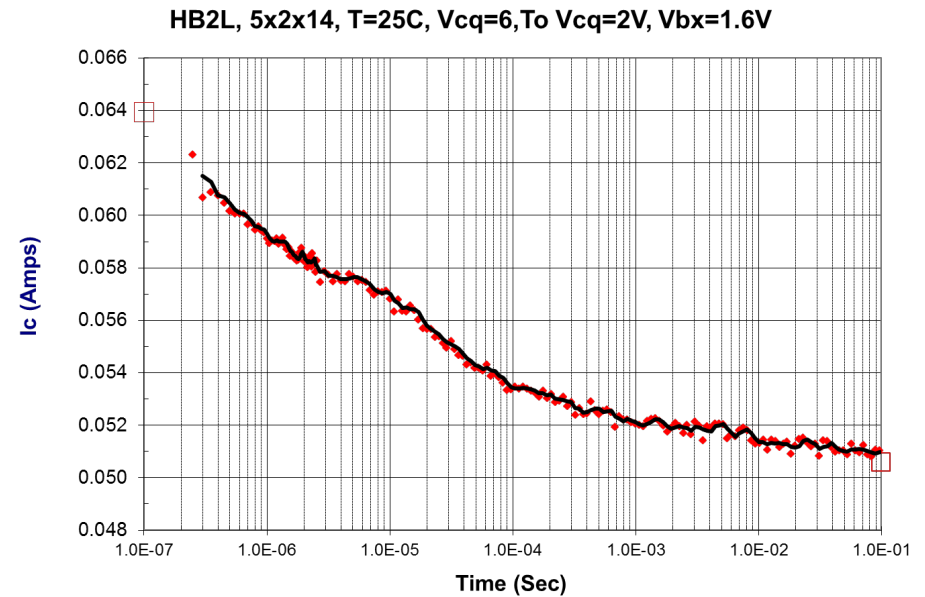
Thermal Conductivity

Transient Thermal Response

Keysight GaAs HBT Test Device (Probe)
Transient pulse applied to Vcollector



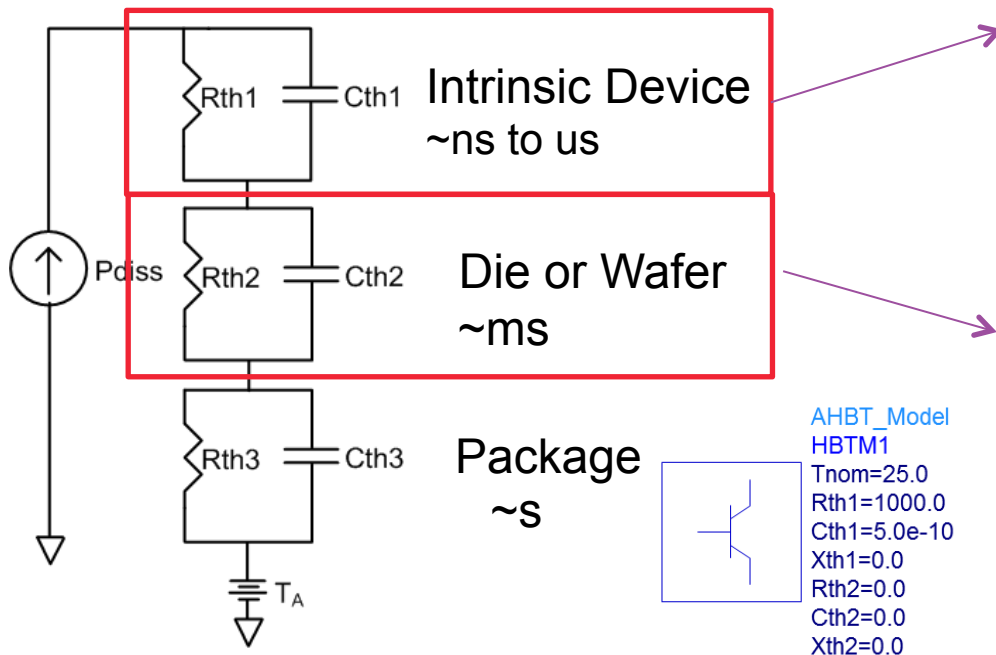
Resulting Thermal Response in Ic
(Current drop shown here is due to dev. cooling)



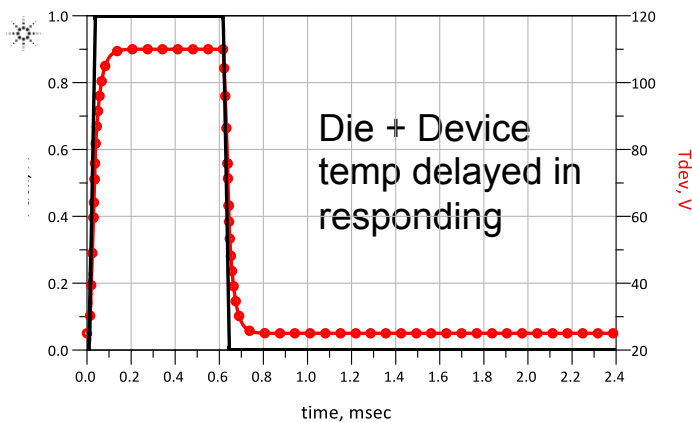
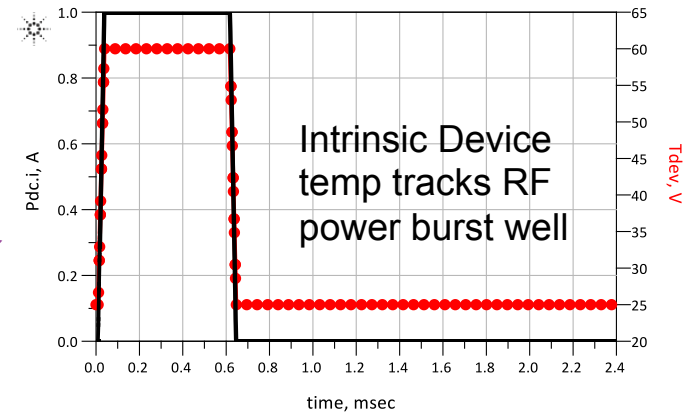
(Log Scale for time)

Lumped Modeling Approach

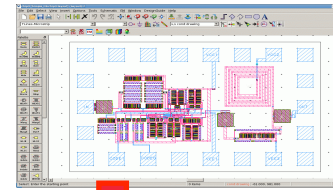
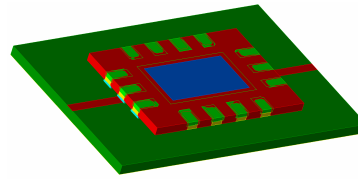
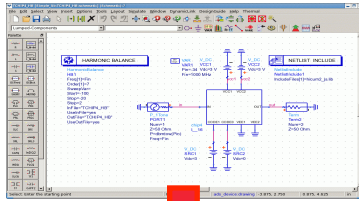
Thermal Network is modeled as a RC Network(s) for fast pulses $\tau_{th} = R_{th} C_{th}$



AHBT_Model
 HBTM1
 Tnom=25.0
 Rth1=1000.0
 Cth1=5.0e-10
 Xth1=0.0
 Rth2=0.0
 Cth2=0.0
 Xth2=0.0

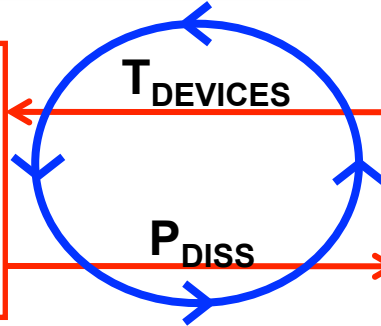


Electro-thermal Modeling Approach

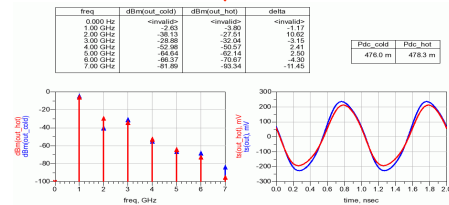


Thermal technology files

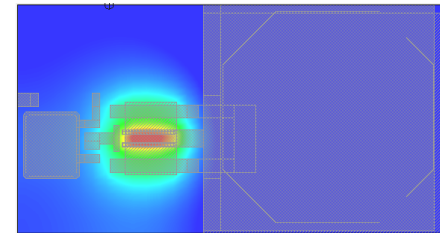
Circuit Simulator
 Read temperatures
 Solve electrical equations
 Write power dissipation



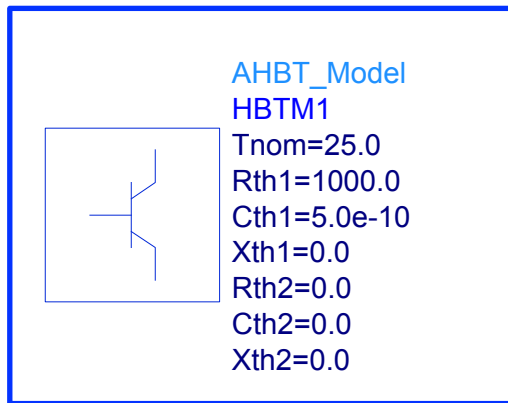
Thermal Simulator
 Read power dissipation
 Solve thermal equation
 Write temperatures



Iteration loop is done automatically until powers and temperatures are self-consistent

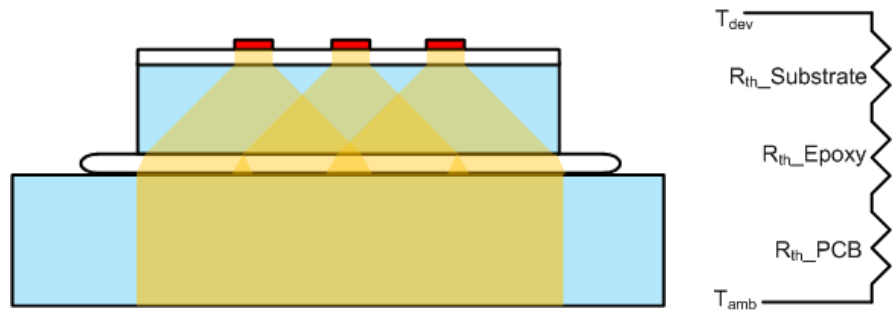
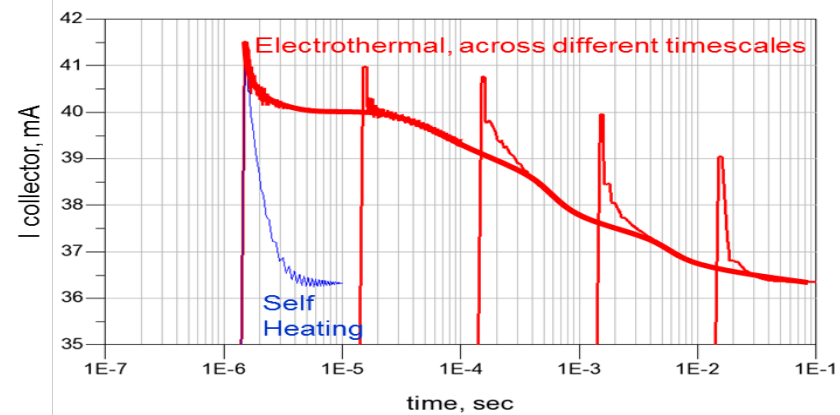


Lumped Thermal RC vs. Full 3D Electro-thermal



VS

Single HBT Device, Beta Drop due to heating



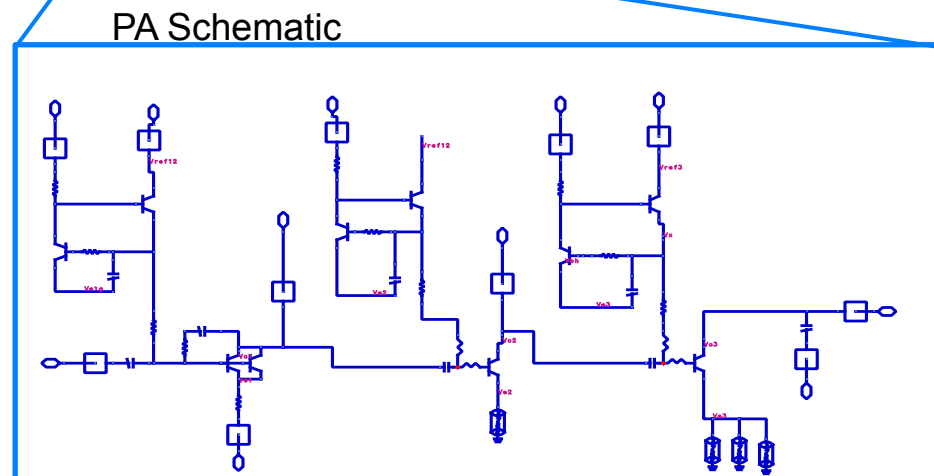
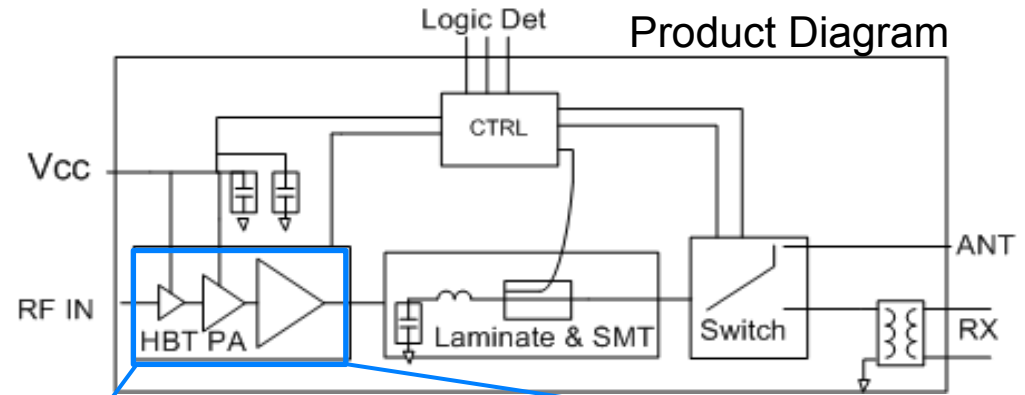
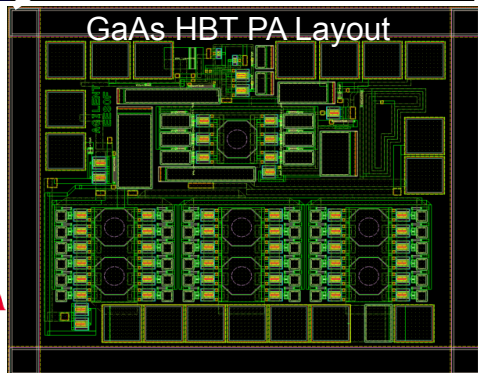
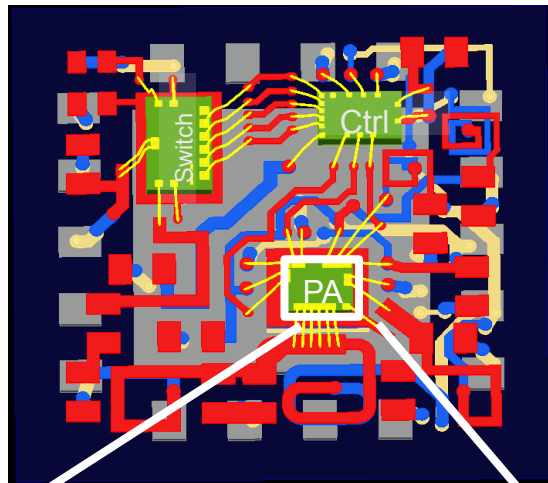
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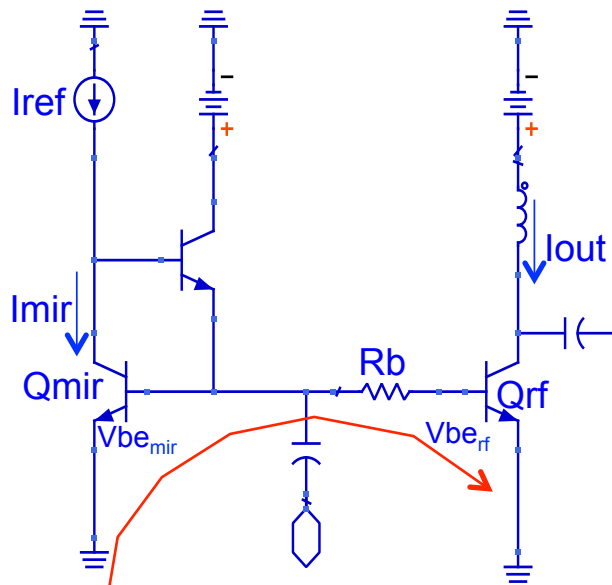
Areas where heating is impactful to PA Design:

- Long Term Failure
- Thermal Stability / Balance
- Device and Circuit Performance
- Memory Effects

Context: Commercial WLAN PA (HBT)



PA Bias Topology



$$V_{be_{mir}} = V_{Rb} + V_{be_{rf}}$$



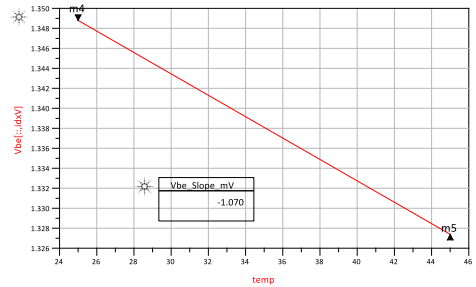
Hold RF Device Temp Constant, vary Tmirror:

$$\frac{dI_{OUT}}{dT_{MIR}} = \frac{dV_{be_{MIR}}}{dT_{MIR}} * \frac{dI_{OUT}}{dV_{be_{MIR}}}$$

$$\frac{dI_{OUT}}{dV_{be_{MIR}}} = \frac{I_s}{V_{T(rf)}} e^{\frac{V_{be_{mir}}}{V_{T(rf)}} - \frac{R_b}{r_{\pi(rf)}}}$$

$$\frac{dV_{be_{MIR}}}{dT_{MIR}} \approx -1.1mV/^{\circ}C$$

Vbe vs. Temperature



Well known characteristic of PN junction diodes: Diode voltage is CTAT

If $T_{MIR} \uparrow$, $V_{be_{MIR}} \downarrow$

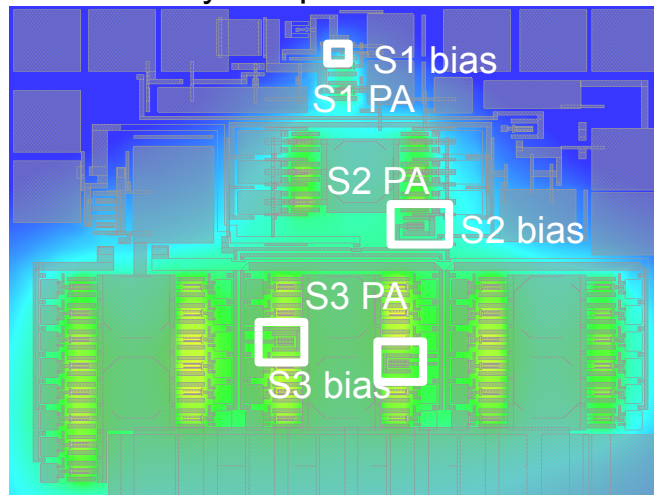
If $V_{be_{MIR}} \downarrow$, $I_{OUT} \downarrow$

If Qmir is cooler than Qrf, the bias current Iout will increase, which can increase the RF gain

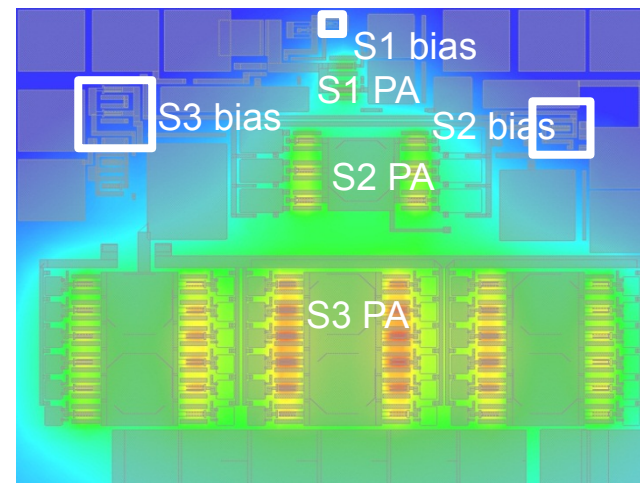
Test Case: Two Different IC Layouts, Identical Schematic

- Here we have two schematically identical WLAN PA layouts to demonstrate the differences between modeling approaches. The three conditions are:
 - Isolated Self Heating Simulation (Static Thermal Network, Internal to AHBT Model)
 - Full Electro-thermal Simulation with moderately thermal-coupled bias networks
 - Full Electro-thermal Simulation with a poorly thermal-coupled bias network

Thermally Coupled Bias Networks



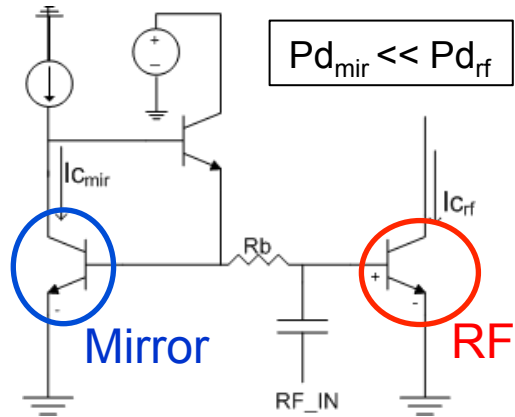
Thermally Decoupled Bias Networks



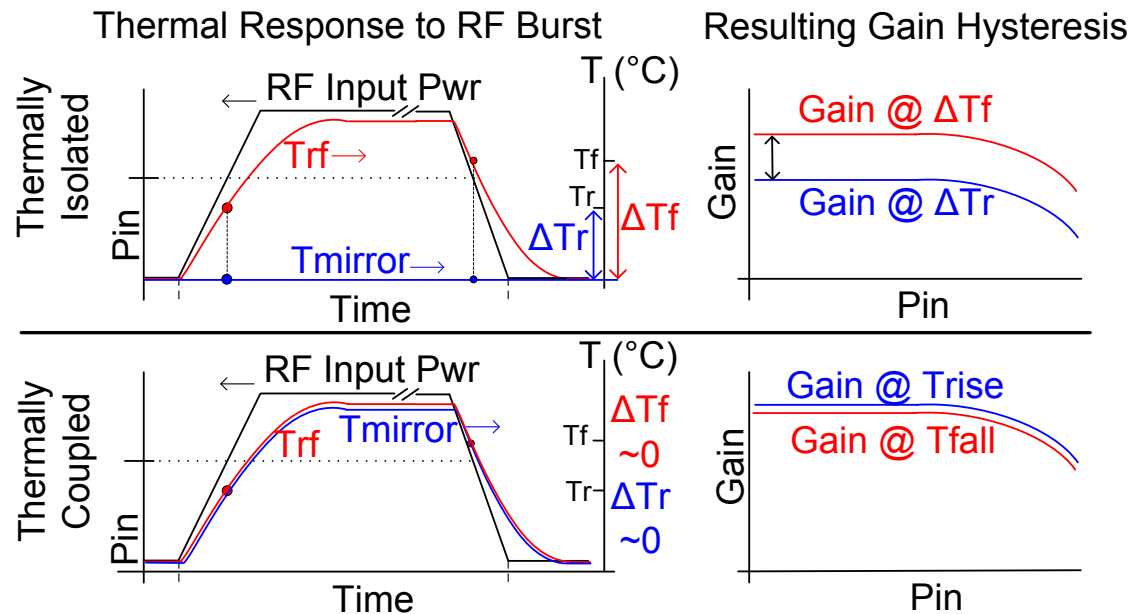
Temperature Coupling and Memory Effects

...Apply a low frequency RF power pulse

Bias Configuration



$T_{mir} < T_{rf}$, $I_{bias} \uparrow$, Gain \uparrow

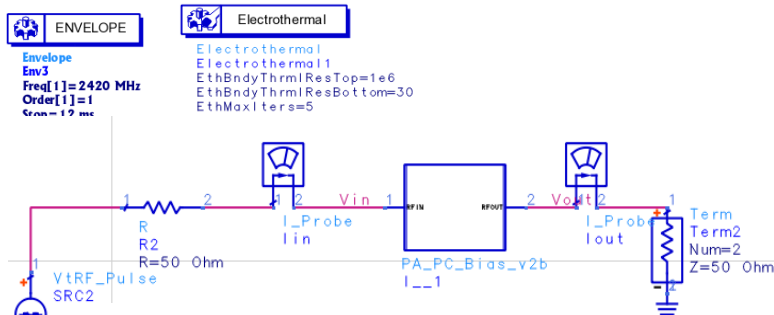


Simulation Results

Transient Simulation with mutual heating between RF and bias device for different layout configurations

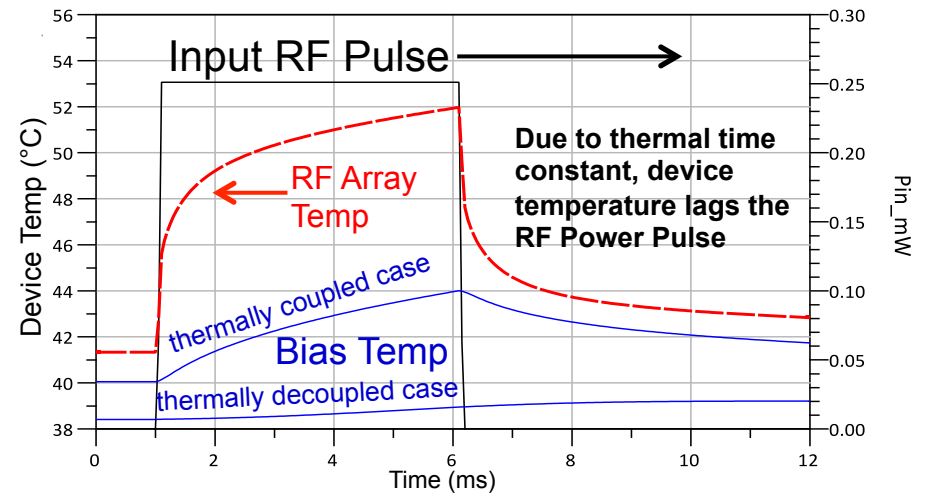
These plots compare:

- Isolated Self Heating Model
- Mutual Heating Model, thermally decoupled
- Mutual Heating Model, thermally coupled

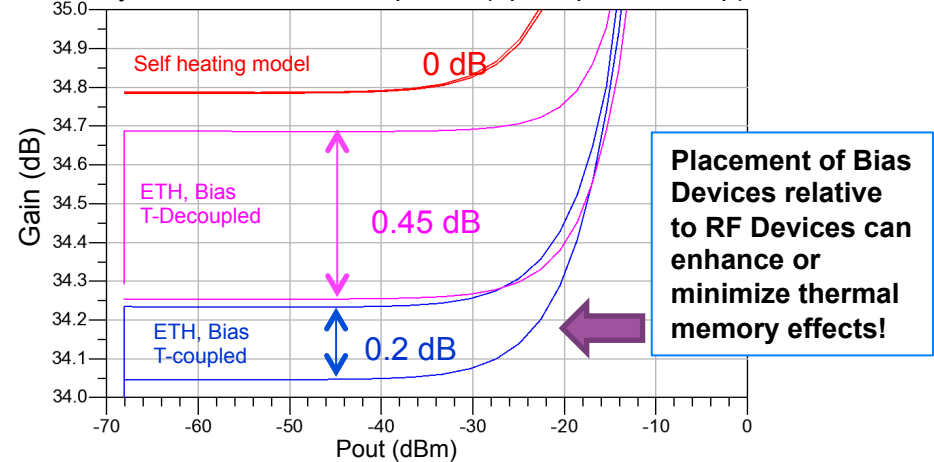


Apply Time Dependent RF Power Burst, Plot gain curves at rising and falling edges

Stage 3: RF Device and Bias Device Reaction to RF Input Pulse



Hysteresis in Gain Response (upramp/downramp)



Closing

- Modeling distributed heating is critical in RF Power Amplifier Design, especially for low frequency phenomena such as memory effects or device-to-device interaction
- Memory effects at low frequencies might be due to:
 - Cross-circuit, layout-dependent mutual heating
 - Distributed heating on longer time scales
- This is a case where full Electro-thermal analysis is useful in the design process because it predicts problems that the intrinsic thermal RC network inside the device model does not

Thanks!

Feel free to contact me with any additional questions:

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